

Appl. No. 08/824,633; Docket No. PHA 51265
Amdt. dated October 12, 2005
Response to Decision from Board of Patent Appeals and
Interferences dated September 29, 2005

Amendments to the Claims

22. *(Cancelled)*

23. *(Currently Amended)* ~~The polishing pad of Claim 22,~~ A polishing pad suitable for chemical mechanical polishing of wafers, comprising:

a circular base layer and an overlying circular top layer, the overlying circular top layer forming the polishing surface of the polishing pad;

wherein the polishing surface of the polishing pad has at least two polishing regions thereon, the at least two polishing regions having distinct polishing characteristics, and wherein the at least two polishing regions are disposed on the polishing pad as concentric annular regions; and

wherein the circular base layer comprises at least two concentric annular regions, each of the at least two base layer concentric annular regions disposed so as to underlie a corresponding one of the at least two polishing regions.

24. *(Previously Presented)* The polishing pad of Claim 23, wherein each of the at least two base layer concentric annular regions has a hardness that is different from the others of the at least two base layer concentric annular regions.

25. *(Previously Presented)* The polishing pad of Claim 23, wherein each of the at least two base layer concentric annular regions has a thickness that is different from the others of the at least two base layer concentric annular regions.

26. *(Currently Amended)* ~~The polishing pad of Claim 22,~~ The polishing pad of Claim 23, wherein the circular top layer comprises at least two concentric annular regions, each of the at least two top layer concentric annular regions disposed so as to correspond with a single one of the at least two polishing regions; and each of the at least two top layer concentric annular regions having different polishing characteristics.

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27. (*Currently Amended*) ~~The polishing pad of Claim 22;~~ The polishing pad of Claim 23, wherein the circular top layer comprises at least two concentric annular regions, each of the at least two top layer concentric annular regions disposed so as to correspond with a single one of the at least two polishing regions; and each of the at least two top layer concentric annular regions having different surface textures.

28. (*Currently Amended*) ~~The polishing pad of Claim 22;~~ The polishing pad of Claim 23, wherein the at least two polishing regions are each of a size such that the wafer can be frictionally engaged with one of the at least two concentric annular polishing regions without simultaneously being engaged with others of the at least two concentric annular polishing regions.

29. (*Cancelled*)

30. (*Currently Amended*) ~~The polishing pad of Claim 29;~~ The polishing pad of Claim 31, wherein the at least two polishing regions are each of a size such that the wafer can be frictionally engaged with one of the at least two parallel linear polishing regions without simultaneously being engaged with others of the at least two parallel linear polishing regions.

31. (*Currently Amended*) ~~The polishing pad of Claim 29;~~ A polishing pad suitable for chemical mechanical polishing of wafers, comprising:

a linear base layer and an overlying linear top layer, the overlying linear top layer forming the polishing surface of the polishing pad;

wherein the polishing surface of the polishing pad has at least two polishing regions thereon, the at least two polishing regions having distinct polishing characteristics, and wherein the at least two polishing regions are disposed on the polishing pad as parallel linear regions; and

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wherein the linear base layer comprises at least two parallel linear regions, each of the at least two base layer parallel linear regions disposed so as to underlie a corresponding one of the at least two polishing regions.

32. *(Previously Presented)* The polishing pad of Claim 31, wherein each of the at least two base layer parallel linear regions has a hardness that is different from the others of the at least two base layer parallel linear regions.

33. *(Previously Presented)* The polishing pad of Claim 31, wherein each of the at least two base layer parallel linear regions has a thickness that is different from the others of the at least two base layer parallel linear regions.

34. *(Currently Amended)* ~~The polishing pad of Claim 29;~~ The polishing pad of Claim 31, wherein the linear top layer comprises at least two parallel linear regions, each of the at least two top layer parallel linear regions disposed so as to correspond with a single one of the at least two polishing regions; and each of the at least two top layer parallel linear regions having different polishing characteristics.

35. *(Currently Amended)* ~~The polishing pad of Claim 29;~~ The polishing pad of Claim 31, wherein the linear top layer comprises at least two parallel linear regions, each of the at least two top layer parallel linear regions disposed so as to correspond with a single one of the at least two polishing regions; and each of the at least two top layer parallel linear regions having different surface textures.